

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI MRF234** is Designed for Large-Signal Amplifier Applications to 100 MHz.

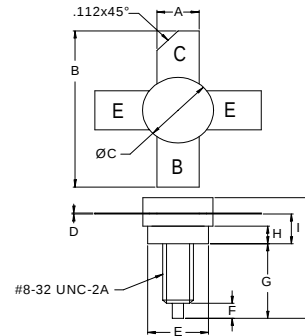
FEATURES:

- Common Emitter
- **Omnigold™** Metalization System
- $P_G = 9.5$ dB min. at 25 W/ 90 MHz

MAXIMUM RATINGS

I_C	4.0 A
V_{CE}	18 V
V_{CB}	36 V
P_{DISS}	70 W @ $T_C = 25^\circ\text{C}$
T_J	-65°C to $+200^\circ\text{C}$
T_{STG}	-65°C to $+150^\circ\text{C}$
θ_{JC}	2.5°C/W

PACKAGE STYLE .380" 4L STUD



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.980 / 24.89	
C	.370 / 9.40	.385 / 9.78
D	.004 / 0.10	.007 / 0.18
E	.320 / 8.13	.330 / 8.38
F	.100 / 2.54	.130 / 3.30
G	.450 / 11.43	.490 / 12.45
H	.090 / 2.29	.100 / 2.54
I	.155 / 3.94	.175 / 4.45
J		.750 / 19.05

CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CES}	$I_C = 200$ mA	36			V
BV_{CEO}	$I_C = 200$ mA	18			V
BV_{EBO}	$I_E = 5.0$ mA	4.0			V
I_{CBO}	$V_{CB} = 15$ V			1.0	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 1.0$ A	5.0			---
C_{ob}	$V_{CB} = 12.5$ V $f = 1.0$ MHz		100	120	pF
G_{PE}	$V_{CC} = 12.5$ V $P_{out} = 25$ W $f = 90$ MHz	9.5			dB
η		55			%